Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	778	polysilicon same silicide same polish$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/12 07:40
L2	63390	(CMP or "chemical mechanical polishing")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/12 07:40
L3	8238	polysilicon and (silicide or silicidation) and gate and pattern$3 and (TiN or "titanium nitride" or "etch stop")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/12 07:46
L6	268	5 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/12 07:44
L7	96	polysilicon same (silicide or silicidation) same pattern$3 same (TiN or "titanium nitride" or "etch stop") same (oxidizing or oxidation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/12 07:46
L9	59	polysilicon same (silicide or silicidation) same pattern$3 same (TiN or "titanium nitride" or "etch stop") same polish$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/12 07:47
L13	220	polysilicon same (silicide or silicidation) same gate same (TiN or "titanium nitride" or "etch stop") same selecti$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/12 07:51
L14	30	barns-chris-e.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/12 07:52

| L15 | 33 | doczy-mark.in. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/12 07:52 |